





### NPN SILICON PLANAR EPITAXIAL SWITCHING TRANSISTORS

\*

2N3903 2N3904

TO-92

TO-92 Plastic Package RoHS compliant

#### **FEATURE:**

1. This product is available in AEC-Q101 Compliant and PPAP Capable also.

Note: For AEC-Q101 compliant products, please use suffix -AQ in the part number while ordering.

**APPLICATIONS:** General Purpose Switching And Amplifier Applications

#### **ABSOLUTE MAXIMUM RATINGS** (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	VALUE	UNIT
Collector Emitter Voltage	$V_{CEO}$	40	V
Collector Base Voltage	$V_{CBO}$	60	V
Emitter Base Voltage	$V_{EBO}$	6.0	V
Collector Current Continuous	I <sub>C</sub>	200	mA
Power Dissipation at Ta=25°C	D	625	mW
Derate Above 25°C	P <sub>D</sub>	5.0	mW/°C
Power Dissipation at Tc=25°C	D	1.5	W
Derate Above 25°C	P <sub>D</sub>	12	mW/°C
Operating and Storage Junction Temperature Range	$T_{j},T_{stg}$	-55 to +150	°C

## THERMAL RESISTANCE

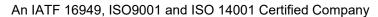
Junction to Case	R <sub>th (j-c)</sub>	83.3	°C/W
Junction to Ambient in free air	R <sub>th (i-a)</sub>	200	°C/W

#### **ELECTRICAL CHARACTERISTICS at** (Ta = 25 °C Unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	Min/ Max	2N3903 2N3904	UNIT
Collector Emitter Voltage	$V_{CEO}$	$I_C=1$ mA, $I_B=0$	Min	40	V
Collector Base Voltage	$V_{CBO}$	I <sub>C</sub> =10m A. I <sub>E</sub> =0	Min	60	V
Emitter Base Voltage	$V_{EBO}$	$I_E=10m A, I_C=0$	Min	6.0	V
Base Cut Off Current	I <sub>BL</sub>	$V_{CE}$ =30V, $V_{EB}$ =3V	Max	50	nA
Collector Cut Off Current	I <sub>CEX</sub>	$V_{CE}$ =30V, $V_{EB}$ =3V	Max	50	nA



# Continental Device India Pvt. Limited







**ELECTRICAL CHARACTERISTICS at** (Ta = 25 °C Unless otherwise specified)

ELECTRICAL STIARACTERIOTIOS AL		Ta = 25 C Offices of ferwise specified)				
PARAMETER	SYMBOL	TEST CONDITIONS	Min/ Max	2N3903	2N3904	UNIT
		I <sub>C</sub> =0.1mA, V <sub>CE</sub> =1V	Min	20	40	
		I <sub>C</sub> =1mA, V <sub>CE</sub> =1V	Min	35	70	
DC Current Gain	h <sub>FE</sub> 1	$I_C=10$ mA, $V_{CE}=1$ V		50~150	100~300	
		$I_C$ =50mA, $V_{CE}$ =1V	Min	30	60	
		$I_C=100$ mA, $V_{CE}=1$ V	Min	15	30	
Collector Emitter Saturation Voltage	V 1	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA	Max	0	.2	V
Collector Efflitter Saturation Voltage	V <sub>CE (sat)</sub> 1	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA	Max	0	.3	V
Base Emitter Saturation Voltage	V 1	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.65	~0.85	V
Base Emilier Saturation voltage	V <sub>BE (sat)</sub> 1	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA	Max	0.	95	V
Transistors Frequency	$f_T$	I <sub>C</sub> =10mA, V <sub>CE</sub> =20V, f=100MHz	Min	250	300	MHz
Output Capacitance	$C_ob$	V <sub>CB</sub> =5V, I <sub>E</sub> =0, f=1MHz	Max	4	.0	pF
Input Capacitance	$C_{ib}$	$V_{EB}$ =0.5V, $I_{C}$ =0, f=1MHz	Max	8.	.0	pF
ALL TEST CONDITION f=1kHz						
Small Signal Current Gain	h <sub>fe</sub>	$I_C=1$ mA, $V_{CE}=10$ V		50~200	100~400	
Input Inpedence	h <sub>ie</sub>	$I_C=1$ mA, $V_{CE}=10$ V		1.0~1.8	1.0~1.10	kΩ
Voltage Feedback Ratio	$h_{re}$	$I_C=1$ mA, $V_{CE}=10$ V		0.1~0.5	0.5~8	x10 <sup>-4</sup>
Out put Admittance	$h_{oe}$	$I_C=1$ mA, $V_{CE}=10$ V		1.0	~40	µmhos
Noise Figure	$N_{F}$	$I_C$ =100m A, $V_{CE}$ =5V, f=1KHz, RS=1KW	Max	6.0	5.0	dB
SWITCHING Time						
Delay time	$t_d$	$V_{CC}$ =3V, $V_{BE}$ =0.5V $I_{C}$ =10mA,	Max	3	35	ns
Rise time	t <sub>r</sub>	I <sub>B1</sub> =1mA Max		3	35	ns
Storage time	t <sub>s</sub>	$V_{CC}$ =3V, $I_{C}$ =10mA	Max	175	200	ns
Fall time	t <sub>f</sub>	I <sub>B1</sub> =1 <sub>B2</sub> =1mA	Max	5	0	ns
-						

#### Note:

1. Pulse Condition: =300µs, Duty Cycle=2%





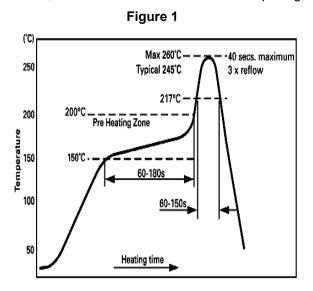


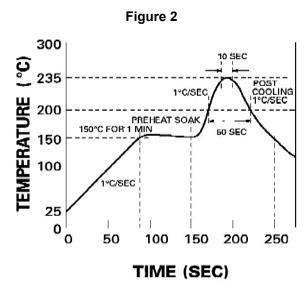
#### **Recommended Reflow Solder Profiles**

The recommended reflow solder profiles for Pb and Pb-free devices are shown below.

Figure 1 shows the recommended solder profile for devices that have Pb-free terminal plating, and where a Pb-free solder is used.

Figure 2 shows the recommended solder profile for devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with a leaded solder.





#### Reflow profiles in tabular form

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~3°C/second	~3°C/second
Preheat  – Temperature Range  – Time	150-170°C 60-180 seconds	150-200°C 60-180 seconds
Time maintained above:  – Temperature  – Time	200°C 30-50 seconds	217°C 60-150 seconds
Peak Temperature	235°C	260°C max.
Time within +0 -5°C of actual Peak	10 seconds	40 seconds
Ramp-Down Rate	3°C/second max.	6°C/second max.

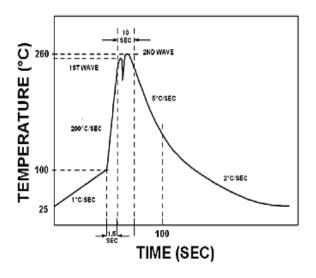




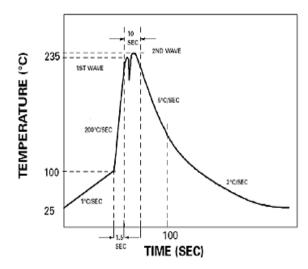


#### **Recommended Wave Solder Profiles**

The Recommended solder Profile For Devices with Pb-free terminal plating where a Pb-free solder is used



The Recommended solder Profile For Devices with Pb-free terminal plating used with leaded solder, or for devices with leaded terminal plating used with leaded solder



#### **Wave Profiles in Tabular Form**

Profile Feature	Sn-Pb System	Pb-Free System
Average Ramp-Up Rate	~200°C/second	~200°C/second
Heating rate during preheat	Typical 1-2, Max 4°C/sec	Typical 1-2, Max 4°C/Sec
Final preheat Temperature	Within 125°C of Solder Temp	Within 125°C of Solder Temp
Peak Temperature 235°C		260°C max.
Time within +0 -5°C of actual Peak 10 seconds		10 seconds
Ramp-Down Rate	5°C/second max.	5°C/second max

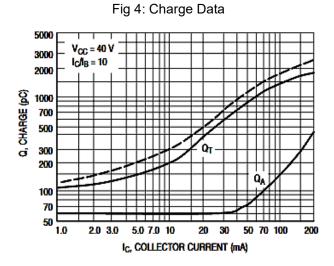


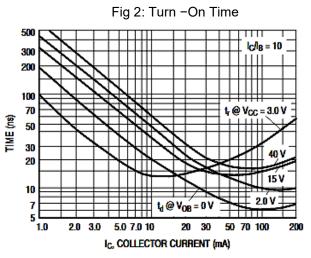


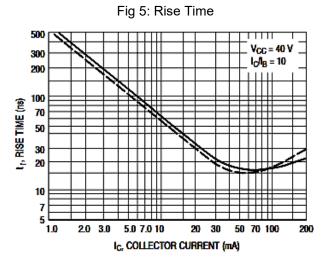
#### TYPICAL CHARACTERISTICS CURVES

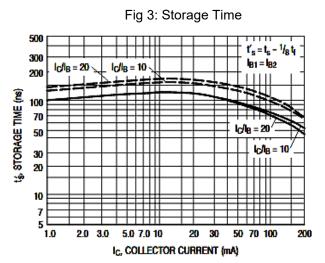
Fig 1: Capacitance 10 7.0 CAPACITANCE (pF) Cibo 2.0 0.2 0.3 0.1 0.5 0.7 1.0 2.0 3.0 5.0 7.0 10 20 30 40

REVERSE BIAS VOLTAGE (VOLTS)

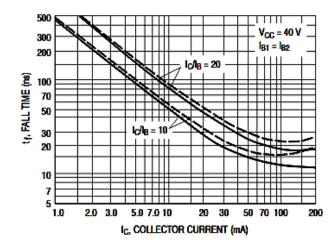
















#### TYPICAL CHARACTERISTICS CURVES

Fig 7: Noise Figure Variation

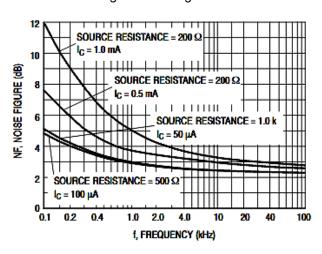


Fig 8: Current Gain

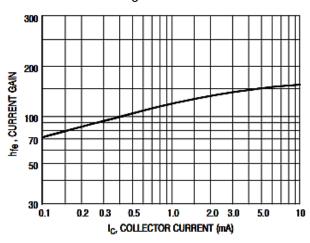


Fig 9: Input Impedance

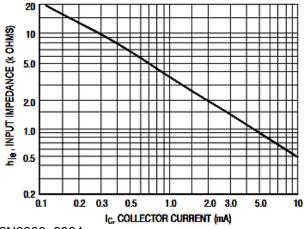


Fig 10: Noise Figure Variation

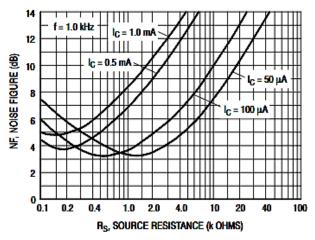


Fig 11: Output Admittance

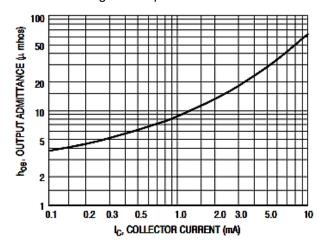
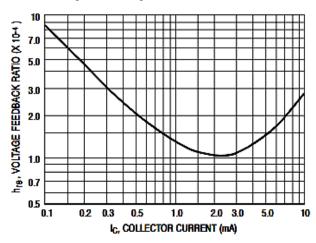


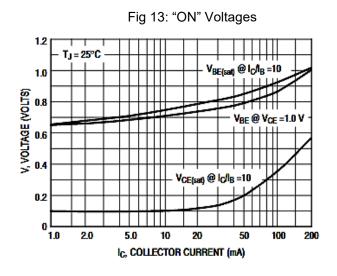
Fig 12: Voltage Feedback Ratio







#### TYPICAL CHARACTERISTICS CURVES



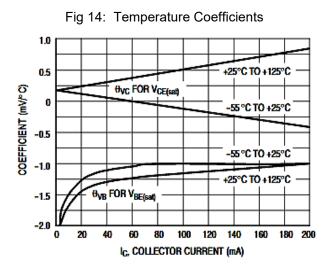


Fig 15: DC Current Gain

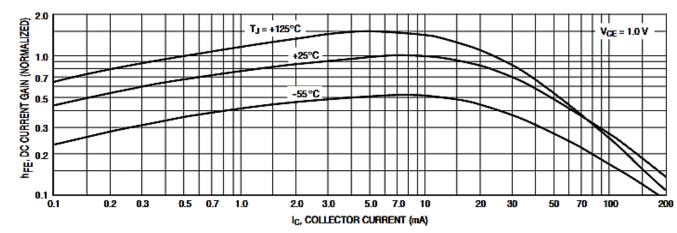
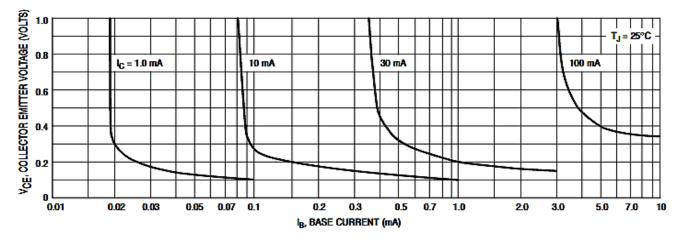


Fig 16: Collector Saturation Region

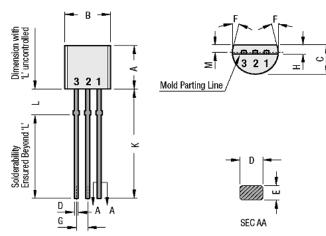






#### **PACKAGE DETAILS**

#### TO-92 Leaded Plastic Package



All dimensions are in mm

#### DIM MIN MAX 4.32 5.33 A 4.45 5.20 В С 3.18 4.19 D 0.40 0.55 Ε 0.30 0.55 F G 1.14 1.40 Н 1.20 1.80 12.5 K L 1.982 2.082 Μ 1.030 1.530

#### **PIN CONFIGURATION**

- 1. Collector
- 2. Base
- 3. Emitter

# **Packaging Information**

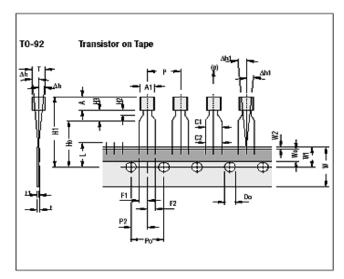
Package/Case		Std. Packing		Inner Carton			Outer Cart	on
Type	Packaging Type	Qty	Qty	Size L x W x H	<b>Gross Weight</b>	Qty	Size L x W x H	<b>Gross Weight</b>
туре		Qty	uty	(cm)	(Kg)	Qty	(cm)	(Kg)
TO-92	Bulk	1,000	5K	19x19x8	1.10	80K	43x40x35	20.0
10-32	T&A	2,000	2K	32x4.5x20	0.70	40K	43x40x35	15.20

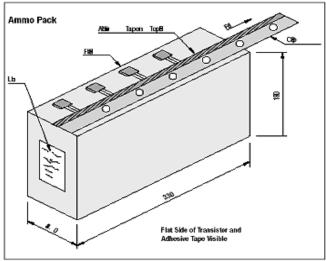






#### TO-92 Tape and Ammo Packaging





All Dimensions are in mm

# **Tape Specifications**

Item description	Symbol
Body width	A1
Body height	A
Body thickness	T
Pitch of component <sup>Cr</sup>	P
Feed hole pitch <sup>§1</sup>	Po
Feed hole center to	
component centre <sup>52</sup>	P2
Comp. alignment, Side view <sup>§3</sup>	Dh
Comp. alignment, Front view <sup>53</sup>	Dh1
Tape width <sup>Cr</sup>	W
Hold down tape width <sup>Cr</sup>	Wo
Hole position	W1
Hold-down tape position	W2
Lead wire clinch height	Но
Component height	H1
Length of snipped leads	L
Feed hole diameter <sup>Cr</sup>	Do
Total tape thickness§4	t
Lead-to-lead distance <sup>Cr</sup>	F1, F2
Stand off	H2
Clinch height	нз
Lead parallelismCr	C1-C2
Pull-out force	(p)

TO-92			
Min	Nom	Max	Tol
4.45		5.20	
4.32		5.33	
3.18		4.19	
	12.7		±1.0
	12.7		±0.3
	6.35		±0.4
	0	1.0	
	0	1.3	
	18		±0.5
	6		±0.2
	9		+0.7 -0.5
0.0		0.7	
	16		±0.5
		24.0	
		11.0	
	4		±0.2
		1.2	
2.4		2.7	
0.45		1.45	
		3.0	
		0.22	
6N			

All Dimensions are in mm

#### Taping Specification

- Maximum alignment deviation between leads not to be greater than 0.20 mm.
- Maximum non-cumulative variation between tape feed holes shall not exceed 1 mm in 20 pitches.
- Hold down tape not to exceed beyond the edge(s) carrier tape and there shall be no exposure of adhesive.
- No more than 3 consecutive missing components is permitted.
- A tape trailer, having at least three feed holes is required after the last component.
- Splices shall not interfere with the sprocket feed holes.
- §1 Cumulative pitch error 1.0 mm/20 pitch.
- §2 To be measured at bottom of clinch.
- §3 At top of body.
- 4 t1 = 0.3 0.6 mm
- Cr Critical Dimension.





# Recommended Product Storage Environment for Discrete Semiconductor Devices

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- · Temperature 5 °C to 30 °C
- · Humidity between 40 to 70 %RH
- · Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- · Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- · Mechanical stress such as vibration and impact shall be avoided.
- · The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

#### **Shelf Life of CDIL Products**

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

#### Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start.

For this, the following JEDEC table may be referred:

	JEDEC MSL Level				
Level	Time	Condition			
1	Unlimited	≤30 °C / 85% RH			
2	1 Year	≤30 °C / 60% RH			
2a	4 Weeks	≤30 °C / 60% RH			
3	168 Hours	≤30 °C / 60% RH			
4	72 Hours	≤30 °C / 60% RH			
5	48 Hours	≤30 °C / 60% RH			
5a	24 Hours	≤30 °C / 60% RH			
6	Time on Label(TOL)	≤30 °C / 60% RH			







#### **Customer Notes**

#### **Component Disposal Instructions**

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

#### **Disclaimer**

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



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